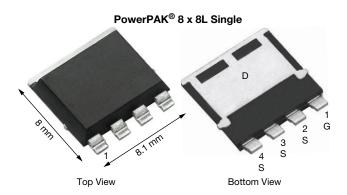


www.vishay.com

Vishay Siliconix

## Automotive N-Channel 60 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY					
V <sub>DS</sub> (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0019				
I <sub>D</sub> (A)	200				
Configuration	Single				
Package	PowerPAK 8 x 8L				

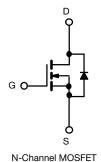
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ABSOLUTE MAXIMUM RATING	GS (T <sub>C</sub> = 25 °C, unless	s otherwise noted	)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	60	V	
Gate-source voltage		$V_{GS}$	± 20	V	
Continuous drain current	T <sub>C</sub> = 25 °C <sup>a</sup>	1	200		
Continuous drain current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	118		
Continuous source current (diode conducti	on)	I <sub>S</sub>	200	Α	
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	500		
Single pulse avalanche current L = 0.1 mH		I <sub>AS</sub>	75		
Single pulse avalanche energy	L=0.11III	E <sub>AS</sub>	281	mJ	
Maximum payar dissination	T <sub>C</sub> = 25 °C	D	150	W	
Maximum power dissipation	T <sub>C</sub> = 125 °C	$P_{D}$	50	VV	
Operating junction and storage temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		
Soldering recommendations (peak temperature) d, e		-	260	C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient P	CB mount c	$R_{thJA}$	50	°C/W
Junction-to-case (drain)		$R_{thJC}$	1	C/VV

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



## www.vishay.com Vishay Siliconix

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static	•							
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = 250 μA	60	-	-	.,	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	· V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.5	3	3.5	V	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V	-	-	1		
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	150		
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	100	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A	-	0.0017	0.0019		
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C	-	-	0.0030	± 100	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C	-	-	0.0035		
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		-	140	-	S	
Dynamic <sup>b</sup>	•							
Input capacitance	C <sub>iss</sub>			-	8170	10 210		
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	3756	4700	pF	
Reverse transfer capacitance	C <sub>rss</sub>			-	70	88		
Total gate charge c	Qg			-	135	180		
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 10 \text{ A}$	-	47	-	nC	
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	14	-		
Gate resistance	$R_g$		f = 1 MHz	0.5	0.9	1.5	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	24	30		
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$	= 30 V, $R_L = 3 \Omega$	-	8	10	]	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A},$	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	47	58	ns	
Fall time <sup>c</sup>	t <sub>f</sub>			-	15	19	]	
Source-Drain Diode Ratings and Ch	aracteristics b							
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	300	А	
Forward voltage	$V_{SD}$	I <sub>F</sub> = 50 A, V <sub>GS</sub> = 0		_	0.82	1.2	V	

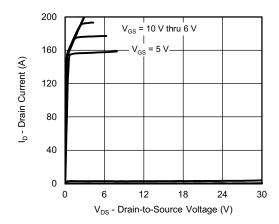
### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

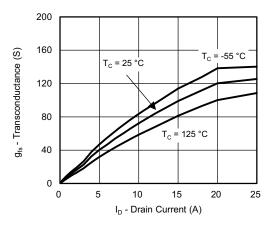
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



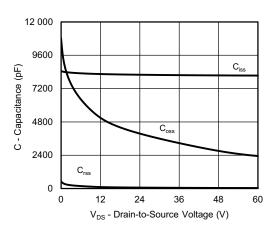
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



### **Output Characteristics**



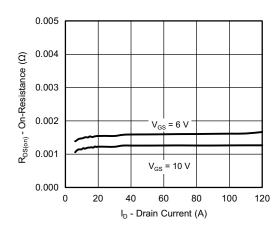
Transconductance



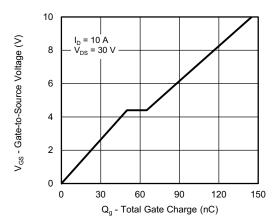
Capacitance

120 100 I<sub>D</sub> - Drain Current (A) 80 60 40 20 T<sub>C</sub> = -55 °C 125 0 0 2 10 4 6 8 V<sub>GS</sub> - Gate-to-Source Voltage (V)

**Transfer Characteristics** 



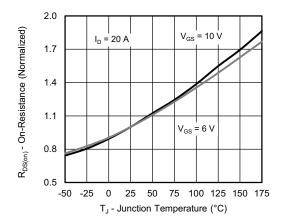
On-Resistance vs. Drain Current



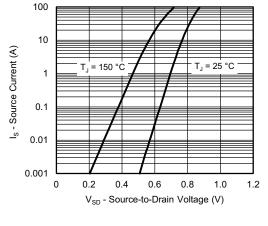
**Gate Charge** 



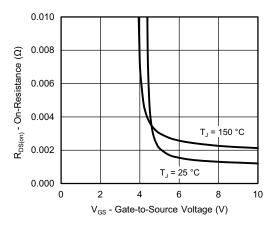
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



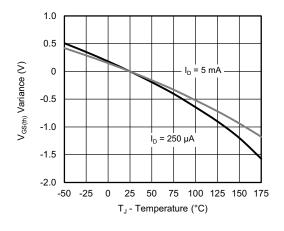
On-Resistance vs. Junction Temperature



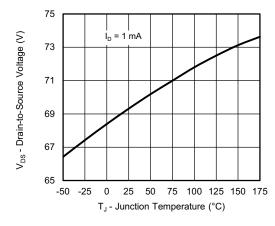
**Source Drain Diode Forward Voltage** 



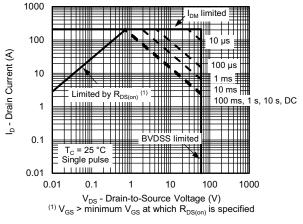
On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 



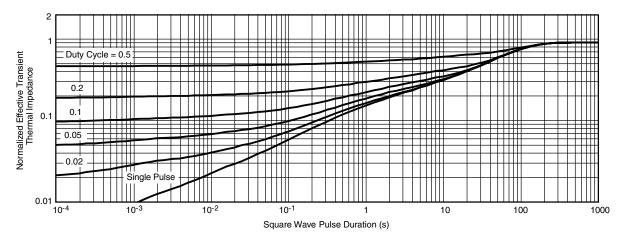
Drain Source Breakdown vs. Junction Temperature



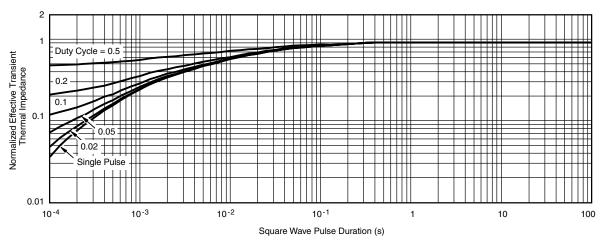
Safe Operating Area



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Ambient

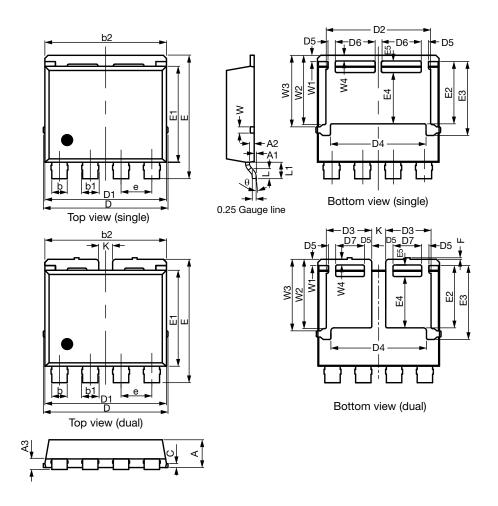


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?75138">www.vishay.com/ppg?75138</a>.



# PowerPAK® 8 x 8L Case Outline



DIM.		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	1.70	1.80	1.90	0.067	0.071	0.075	
A1	0.00	0.08	0.13	0.000	0.003	0.005	
A2	0.25	0.30	0.35	0.010	0.012	0.014	
A3	0.55	0.62	0.70	0.022	0.024	0.028	
b	0.92	1.00	1.08	0.036	0.039	0.043	
b1	1.02	1.10	1.18	0.040	0.043	0.046	
b2	7.80	7.90	8.00	0.307	0.311	0.315	
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	8.00	8.10	8.25	0.315	0.319	0.325	
D1	7.80	7.90	8.00	0.307	0.311	0.315	
D2	6.70	6.80	6.90	0.264	0.268	0.272	
D3	2.85	2.95	3.05	0.112	0.116	0.120	
D4	6.11	6.21	6.31	0.241	0.244	0.248	
D5	0.37	0.47	0.57	0.015	0.019	0.022	
D6	2.49	2.59	2.69	0.098	0.102	0.106	
D7	1.76	1.86	1.96	0.069	0.073	0.077	

Revision: 16-Oct-17 1 Document Number: 67734





www.vishay.com

Vishay Siliconix

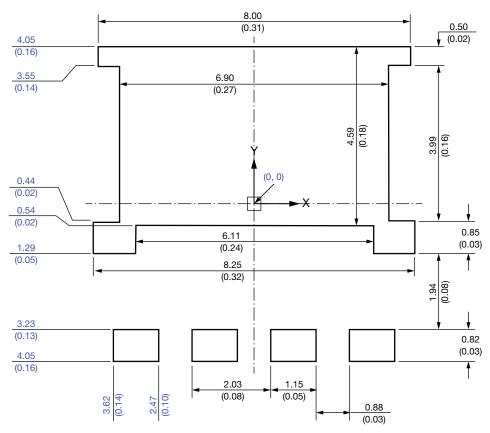
DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
е	1.95	2.00	2.05	0.077	0.079	0.081	
E	7.90	8.00	8.10	0.311	0.315	0.319	
E1	6.12	6.22	6.32	0.241	0.245	0.249	
E2	3.94	4.04	4.14	0.140	0.159	0.163	
E3	4.69	4.79	4.89	0.185	0.189	0.193	
E4	3.23	3.33	3.43	0.127	0.131	0.135	
E5	0.65	0.75	0.85	0.026	0.030	0.033	
F	0.00	0.10	0.15	0.000	0.004	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K	0.80	0.90	1.00	0.031	0.035	0.039	
W	0.30	0.40	0.50	0.012	0.016	0.020	
W1	0.30	0.40	0.50	0.012	0.016	0.020	
W2	4.39	4.49	4.59	0.173	0.177	0.181	
W3	4.54	4.64	4.74	0.179	0.183	0.187	
W4	0.32	0.37	0.42	0.013	0.015	0.017	
θ	6°	10°	14°	6°	10°	14°	

C17-1388-Rev. B, 16-Oct-17

DWG: 6026



# Recommended Minimum PADs for PowerPAK® 8 x 8L Single



#### Dimensions in millimeters (inches)

### Note

· Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



## **Legal Disclaimer Notice**

Vishay

## **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.